

MC74VHC08

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_{in}	DC Input Voltage	-0.5 to +7.0	V
V_{out}	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Diode Current	-20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Packages [†] TSSOP Package [†]	500 450	mW
T_{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

[†]Derating – SOIC Packages: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	5.5	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature	-55	+125	°C
t_r, t_f	Input Rise and Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	$T_A = 25^\circ\text{C}$			$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 $V_{CC} \times 0.7$			1.50 $V_{CC} \times 0.7$		V
V_{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 $V_{CC} \times 0.3$		0.50 $V_{CC} \times 0.3$	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH}$ or V_{IL} $I_{OH} = -4.0 \text{ mA}$ $I_{OH} = -8.0 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL} $I_{OL} = 4.0 \text{ mA}$ $I_{OL} = 8.0 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
I_{in}	Maximum Input Leakage Current	$V_{in} = 5.5 \text{ V or GND}$	0 to 5.5			± 0.1		± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20.0	μA

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$			$T_A = -55^\circ\text{C to } 125^\circ\text{C}$		Unit
			Min	Typ	Max	Min	Max	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 15$ pF $C_L = 50$ pF		6.2 8.7	8.8 12.3	1.0 1.0	10.5 14.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 15$ pF $C_L = 50$ pF		4.3 5.8	5.9 7.9	1.0 1.0	7.0 9.0	
C_{in}	Maximum Input Capacitance			4	10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 1)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		18	

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPER)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/4$ (per gate). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

Symbol	Characteristic	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	-0.3	-0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

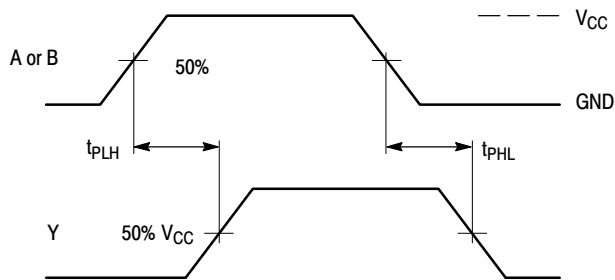
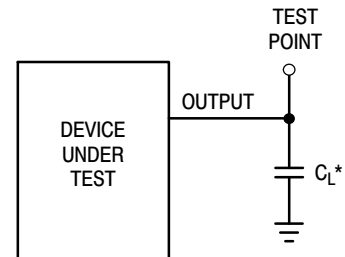


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

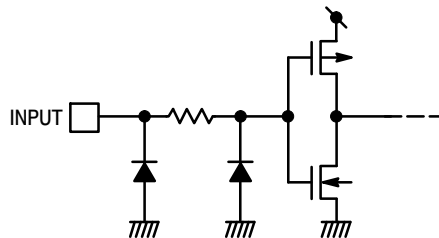


Figure 5. Input Equivalent Circuit

MC74VHC08

ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC08DR2	SOIC-14	2500 Units / Tape & Reel
MC74VHC08DR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
MC74VHC08DTR2	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC08DTR2G	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC08MEL	SOEIAJ-14	2000 Units / Tape & Reel
MC74VHC08MELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel

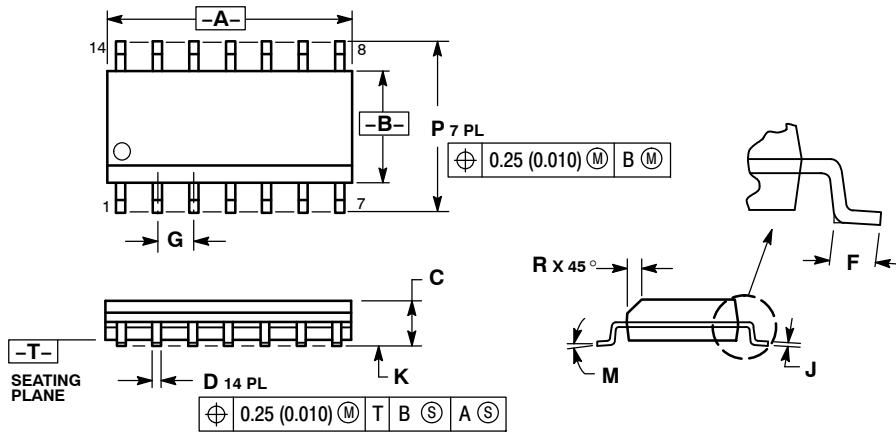
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

MC74VHC08

PACKAGE DIMENSIONS

SOIC-14
CASE 751A-03
ISSUE J

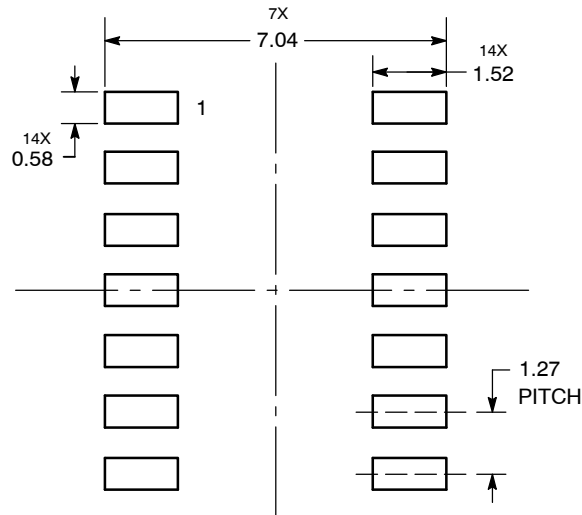


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT

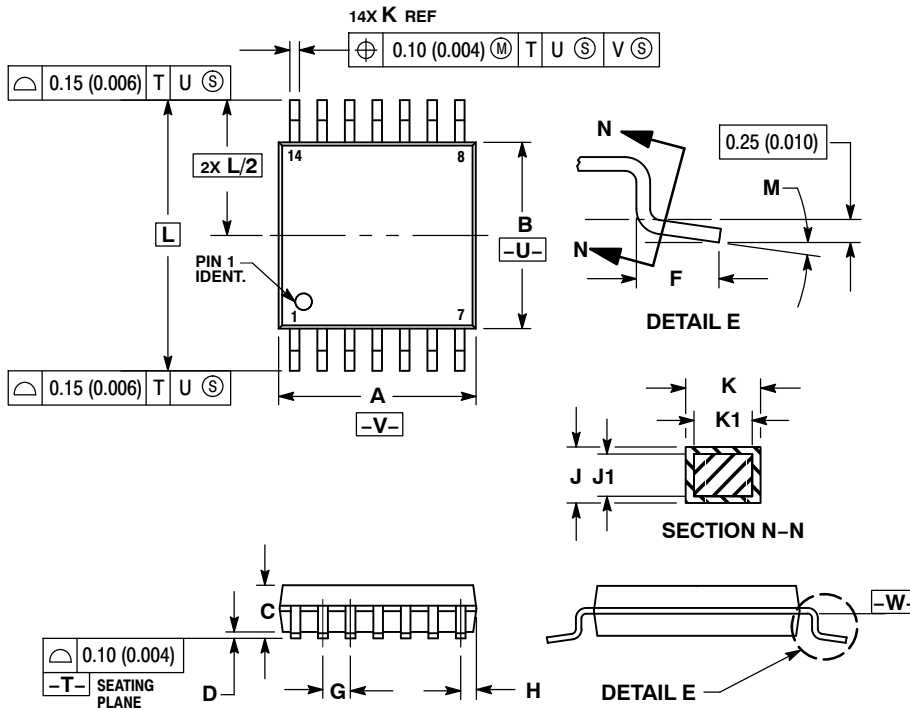


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC74VHC08

PACKAGE DIMENSIONS

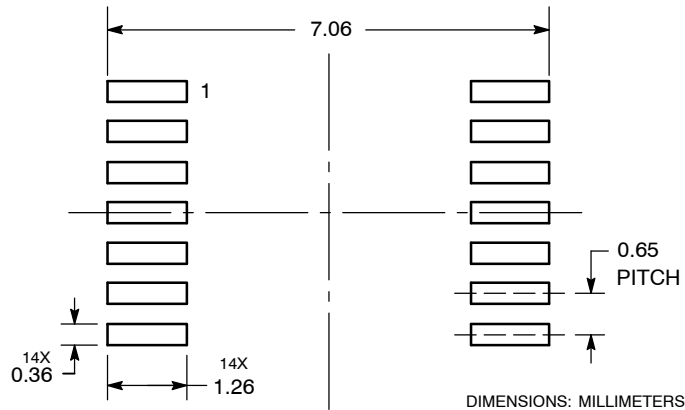
TSSOP-14
CASE 948G-01
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
M	0°	8°	0°	8°

SOLDERING FOOTPRINT

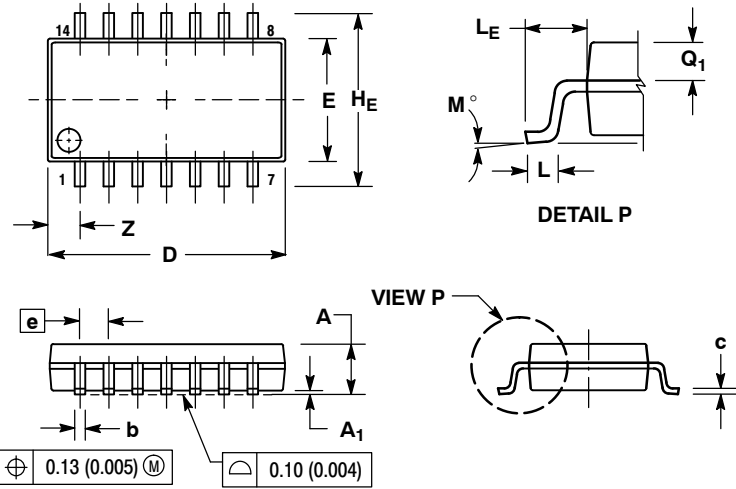


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC74VHC08

PACKAGE DIMENSIONS

SOEIAJ-14
CASE 965-01
ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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